



**WMH-5**

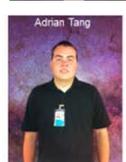
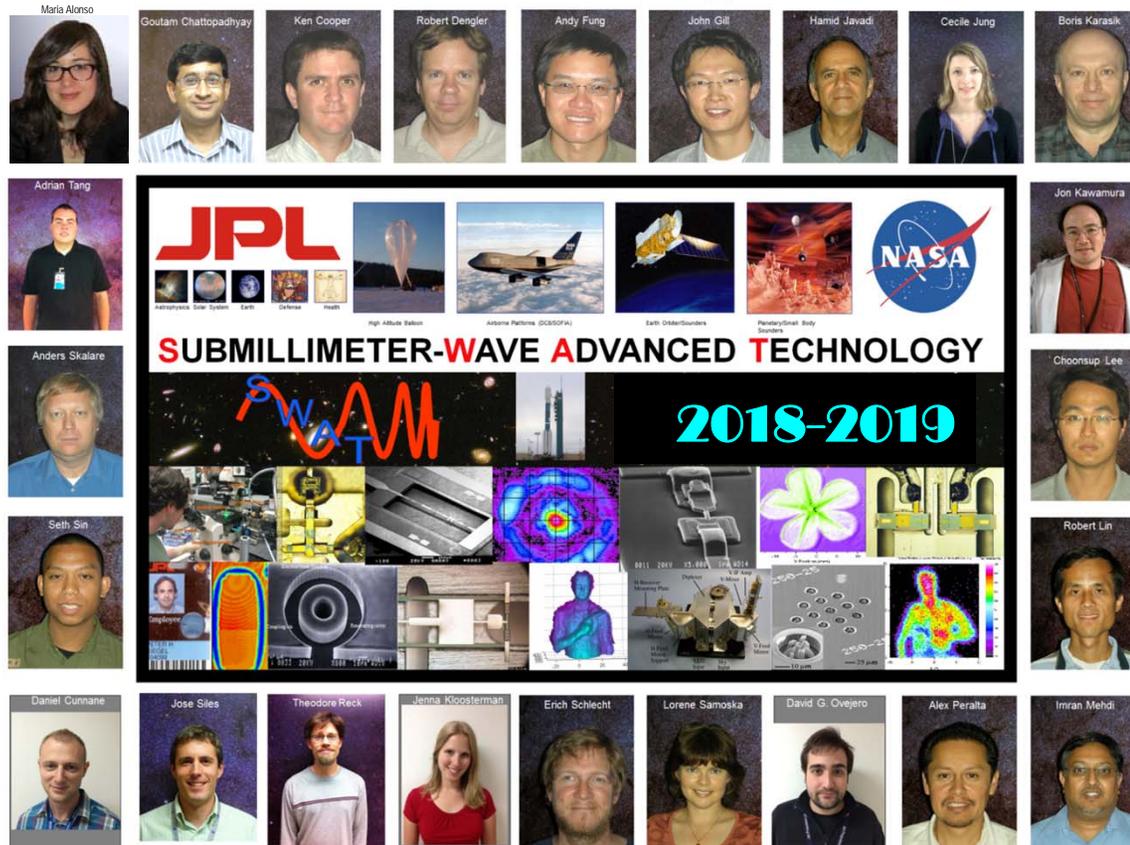
# Packaging and Integration Solutions at Terahertz Frequencies

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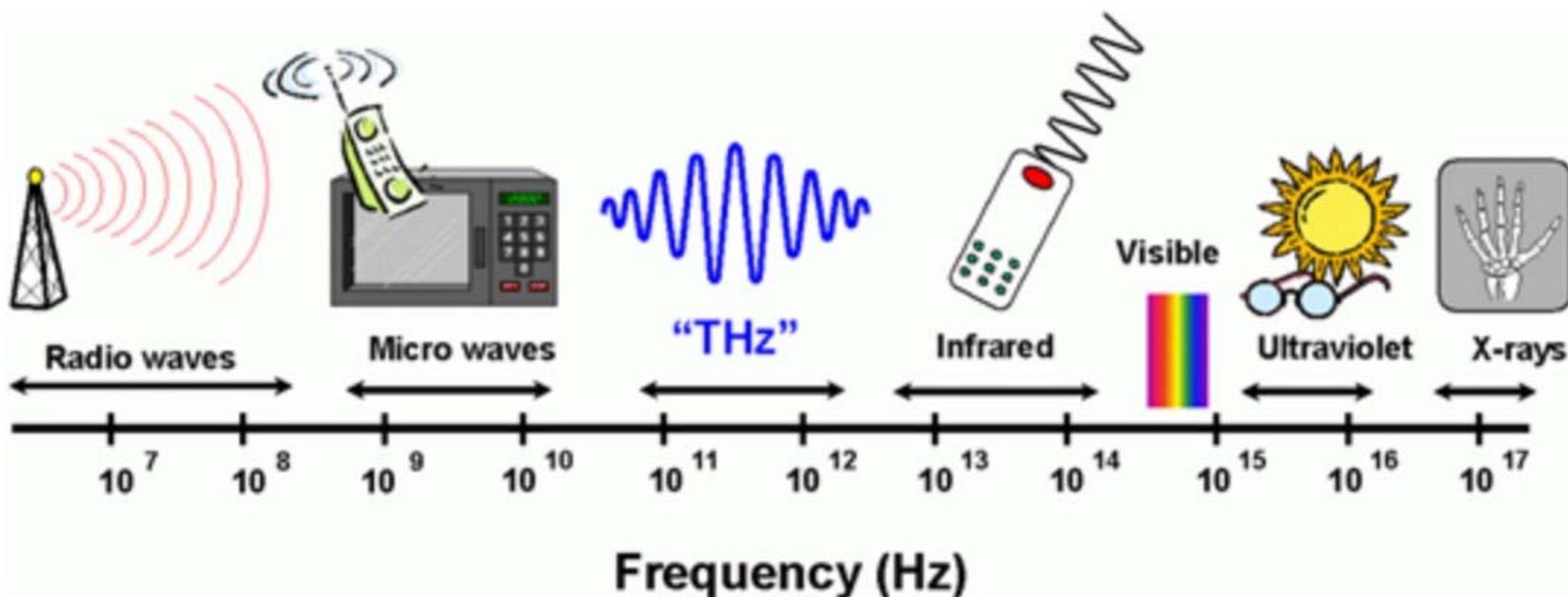


# Acknowledgement



This work was carried out at the California Institute of Technology, Jet Propulsion Laboratory, under contract with the National Aeronautics and Space Administration.

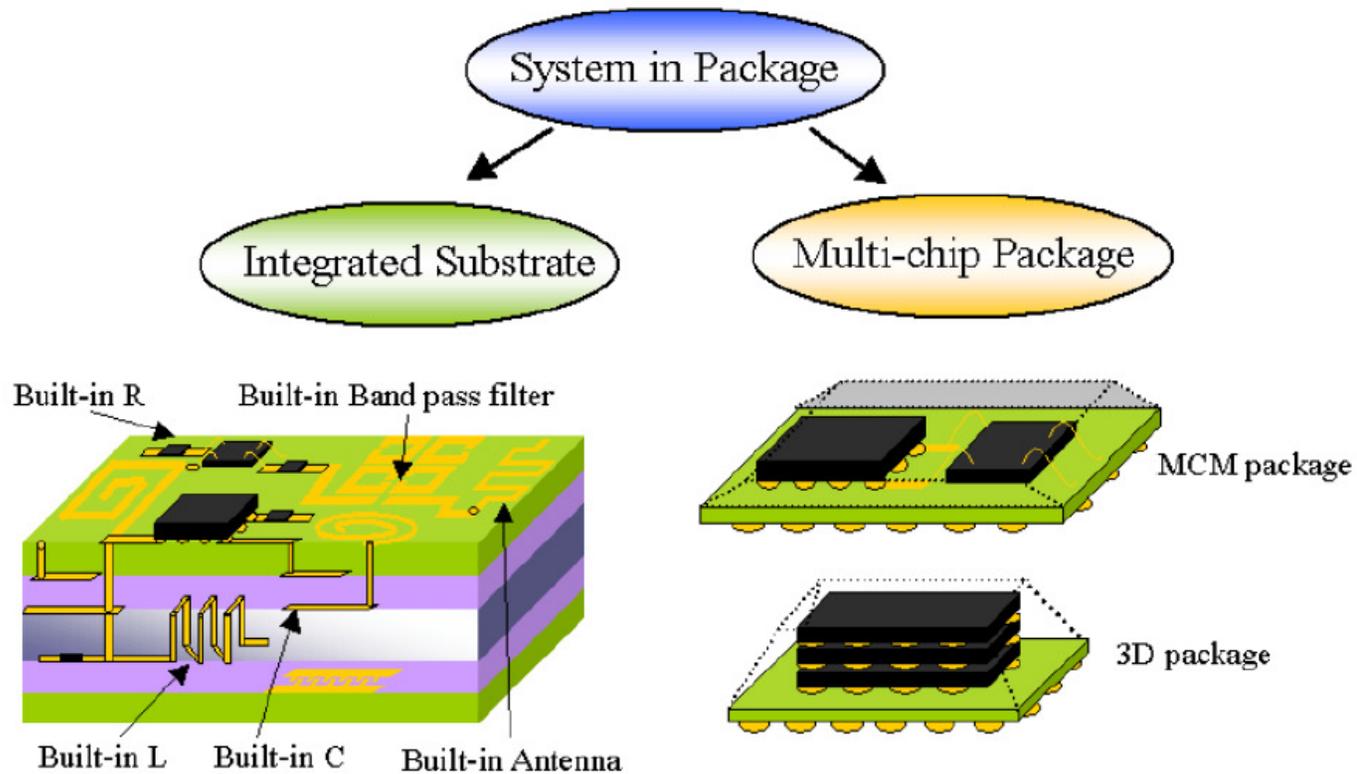
# Terahertz (Submillimeter) Waves



**Loosely defined:  $1 \text{ mm} > \lambda > 100 \text{ } \mu\text{m}$  ( $300 \text{ GHz} < \nu < 3 \text{ THz}$ )**

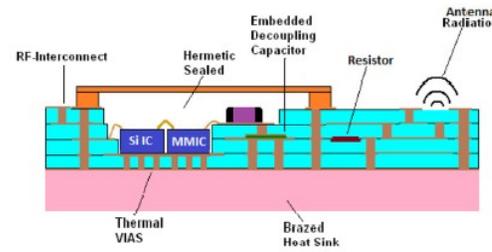
Most of the radiation in the Universe is emitted at submillimeter-wavelengths, peaking at 3 THz.

# Packaging at Millimeter-Waves

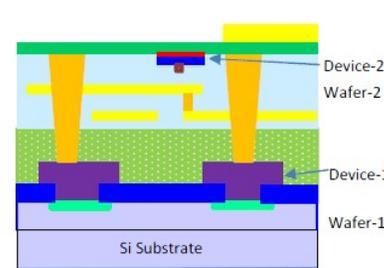


## Different System-on-Package (SOP) Technologies

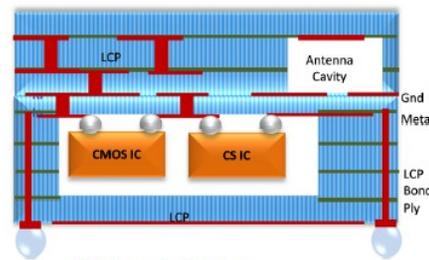
# Packaging at Millimeter-Waves



(a) Ceramic/LTCC



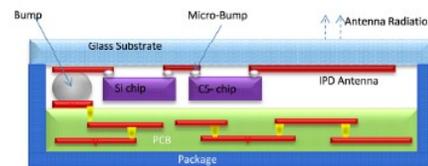
(d) Wafer-scale



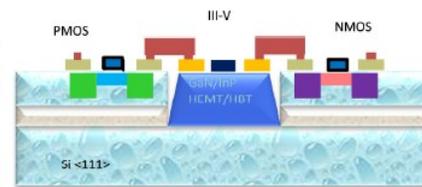
(b) Organic/Laminate



(e) Chiplets



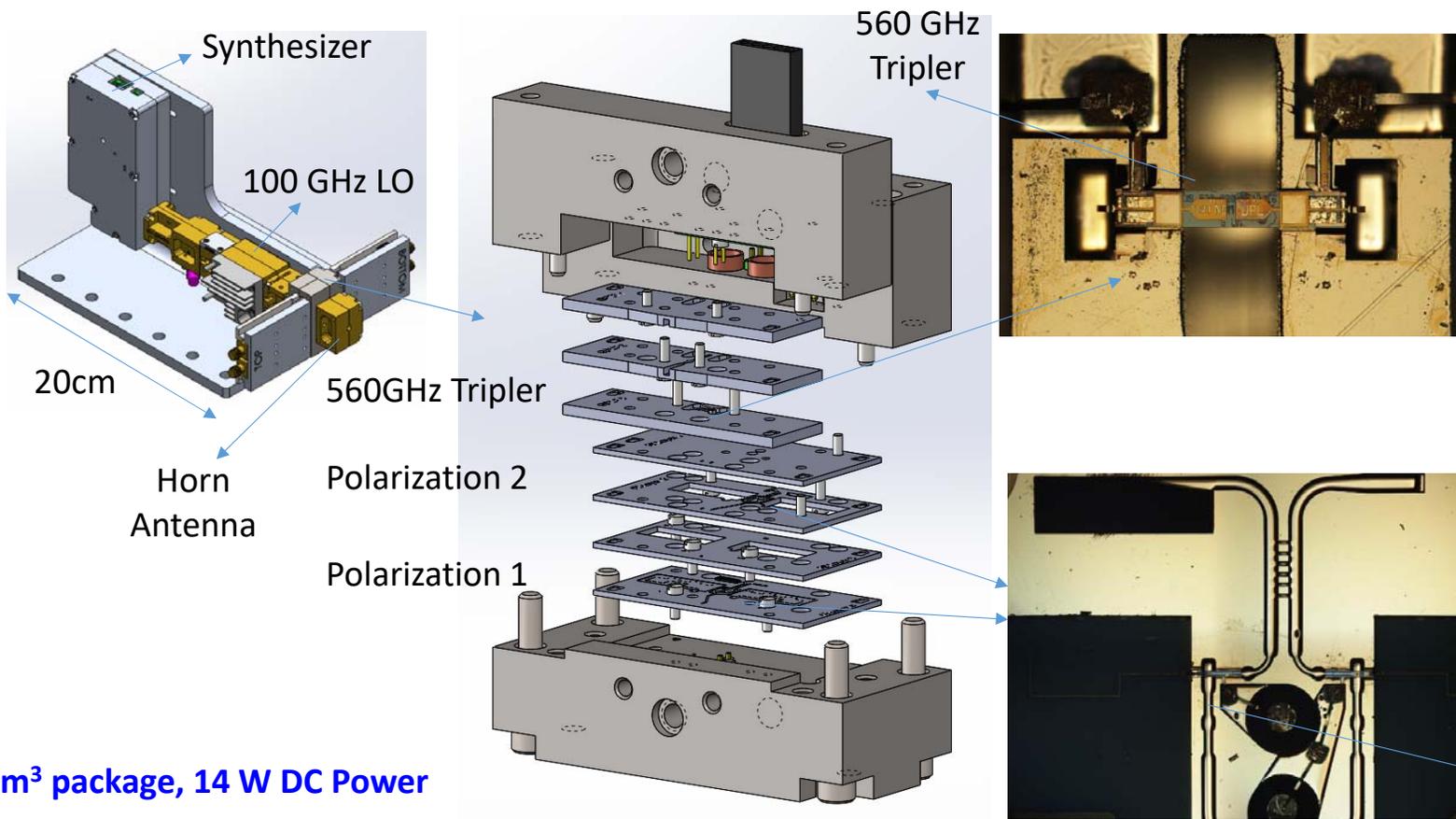
(c) IPD (Si/Glass)



(f) Monolithic

Multi-layer heterogeneous integration: Ceramic LTCC based, Organic Laminate based, Si/Glass based, Wafer-scale, Chiplets based. (Ref: K. Samanta)

# Packaging at Submillimeter-Waves



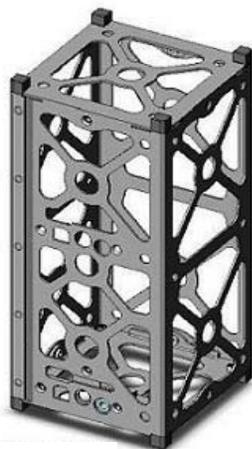
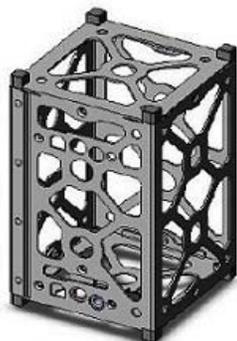
20x15x10 cm<sup>3</sup> package, 14 W DC Power

# CubeSat and SmallSat Platforms

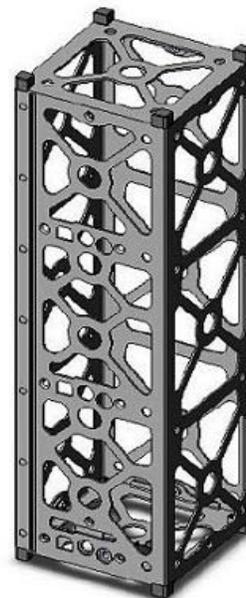
## What are CubeSats?

Cubes of 10 cm x 10 cm x 10 cm: 1 U

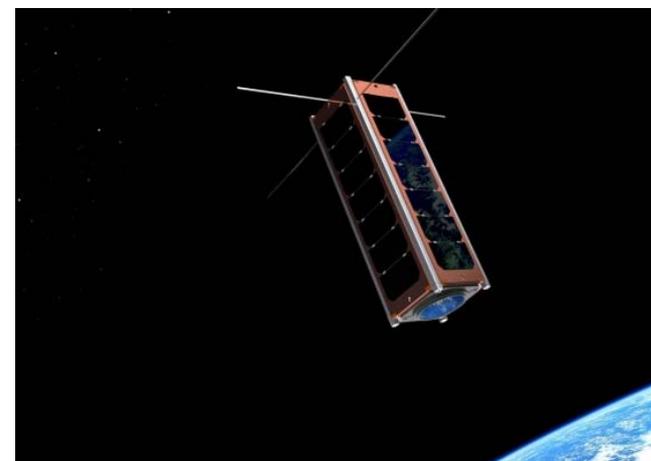
1U



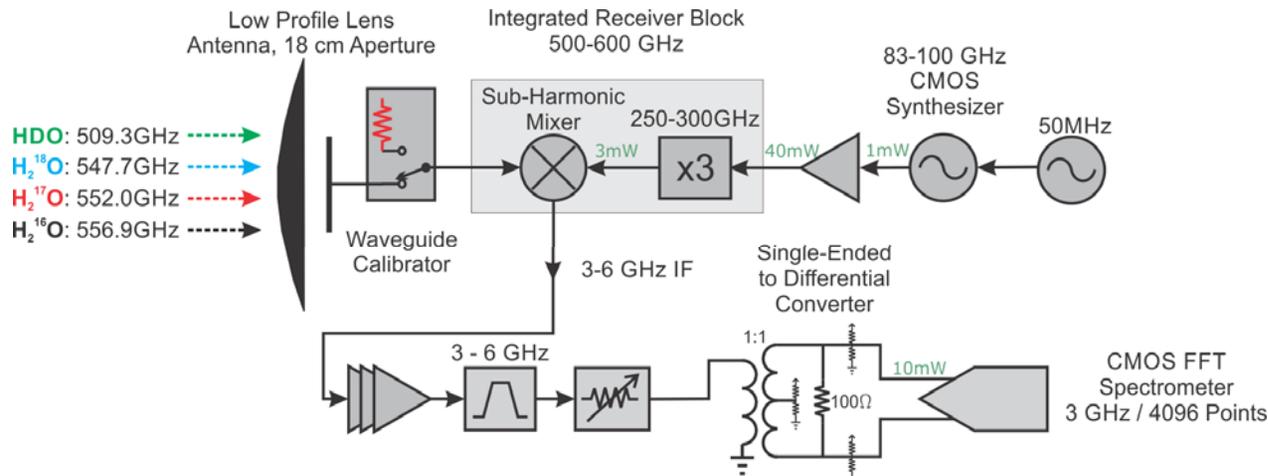
3U



A shoe-box size satellite: includes navigation, communications, antennas, solar panels, and instruments, all on the CubeSat!



# Typical Terahertz Systems



- High-resolution room temperature heterodyne spectrometer 500-600 GHz band
- Low-profile ~18 cm diameter aperture antenna and feed
- Low-power CMOS based W-band synthesizer
- GaAs Schottky diode based subharmonic mixers and frequency multipliers
- CMOS based 3 GHz bandwidth, 4096 channels, low-power FFT spectrometer
- The target mass and power for the instrument is less than 2 kg and <5 W.

# Silicon Micromachining

## Silicon Micromachining

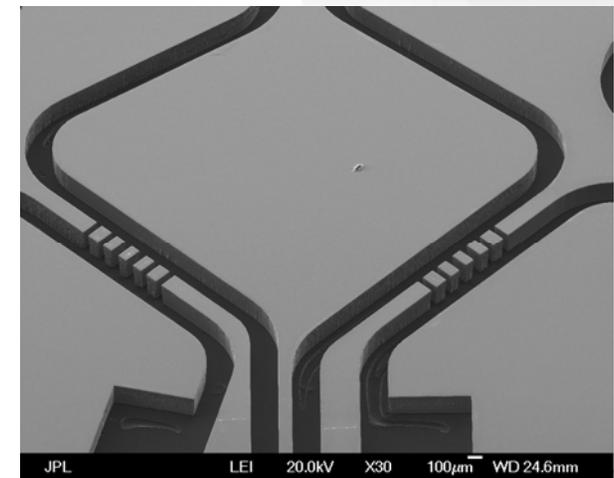
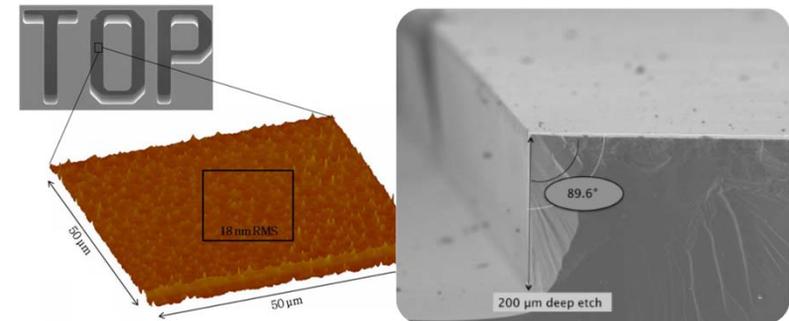
- Etch silicon wafer with plasma using a photolithographic pattern

## Advantages:

- Potential for lower cost because of batch-processed device fabrication, yielding better uniformity too.
- Lithographically precise feature definitions
- Integration of bias & IF lines on silicon itself. Future potential for integrated CMOS silicon devices.
- Potential for higher density 2D transceiver arrays.

## Disadvantages:

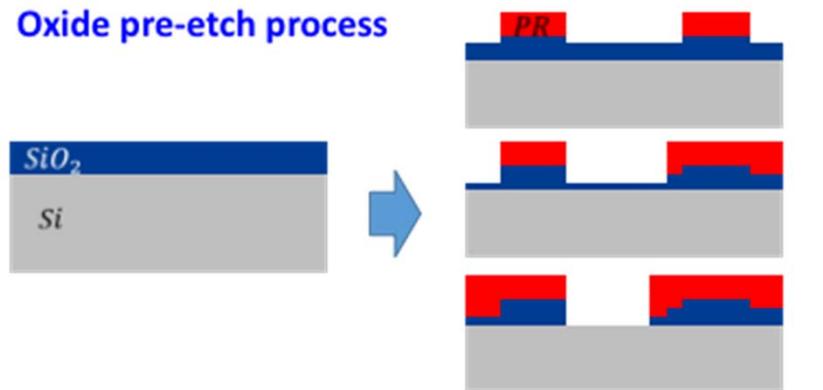
- Immature technology: need for process development:  
**Not anymore!**
- Challenge of wafer alignment.



# Deep Reactive Ion Etching

- Use of an optimized **Bosch** process to etch the silicon: alternative exposures of  $SF_6$  and  $C_4F_8$  plasmas.

## Oxide pre-etch process



- Use of  $SiO_2$  as **hard mask** (selectivity 150:1) to etch  $Si$
- Use of photoresist to do the  $SiO_2$  patterning
- Etching of the differential pattern to ensure precise control
- Etching using Inductive Couple Plasma (ICP) process

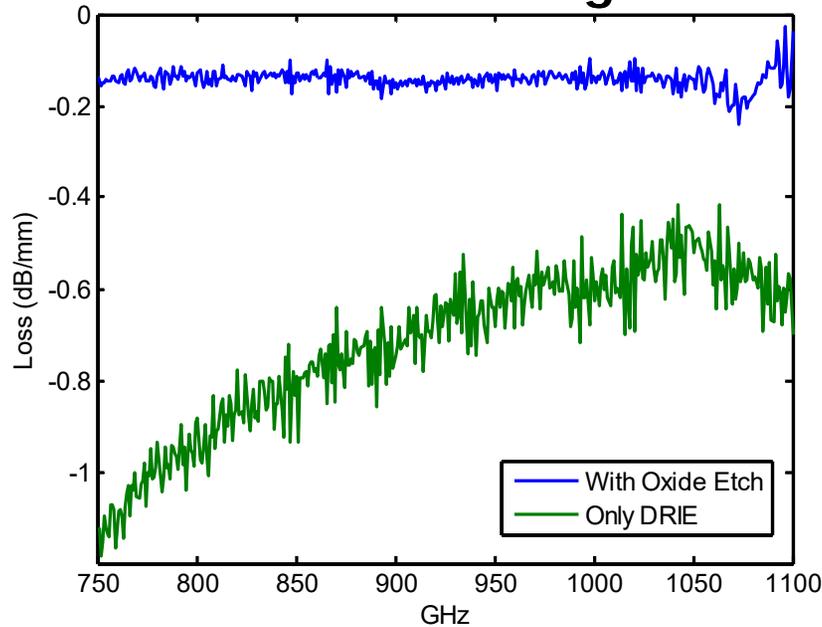


## DRIE process

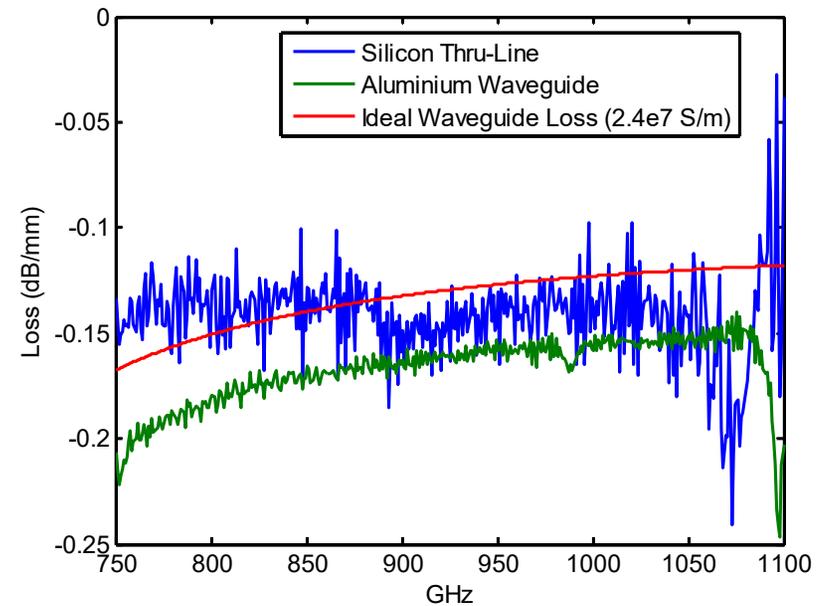
- DRIE process to etch the silicon, with oxide as the sole mask
- No photoresist

# Deep Reactive Ion Etching

## Effect of Etch Roughness

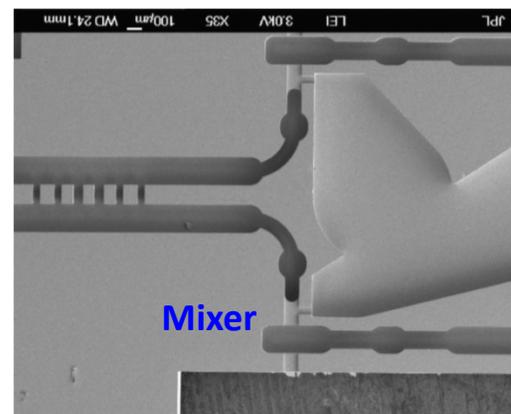
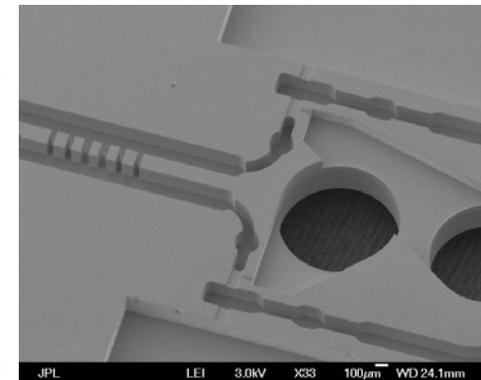
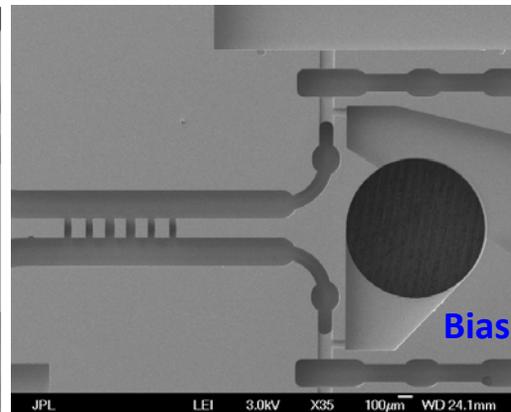
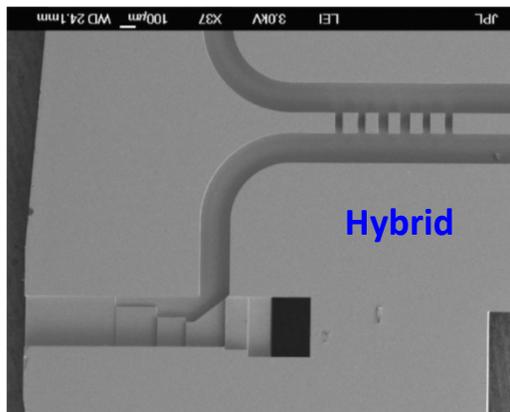
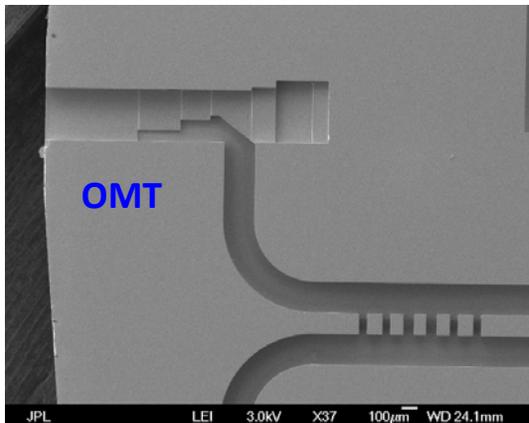


## Waveguide Loss: Thru Lines



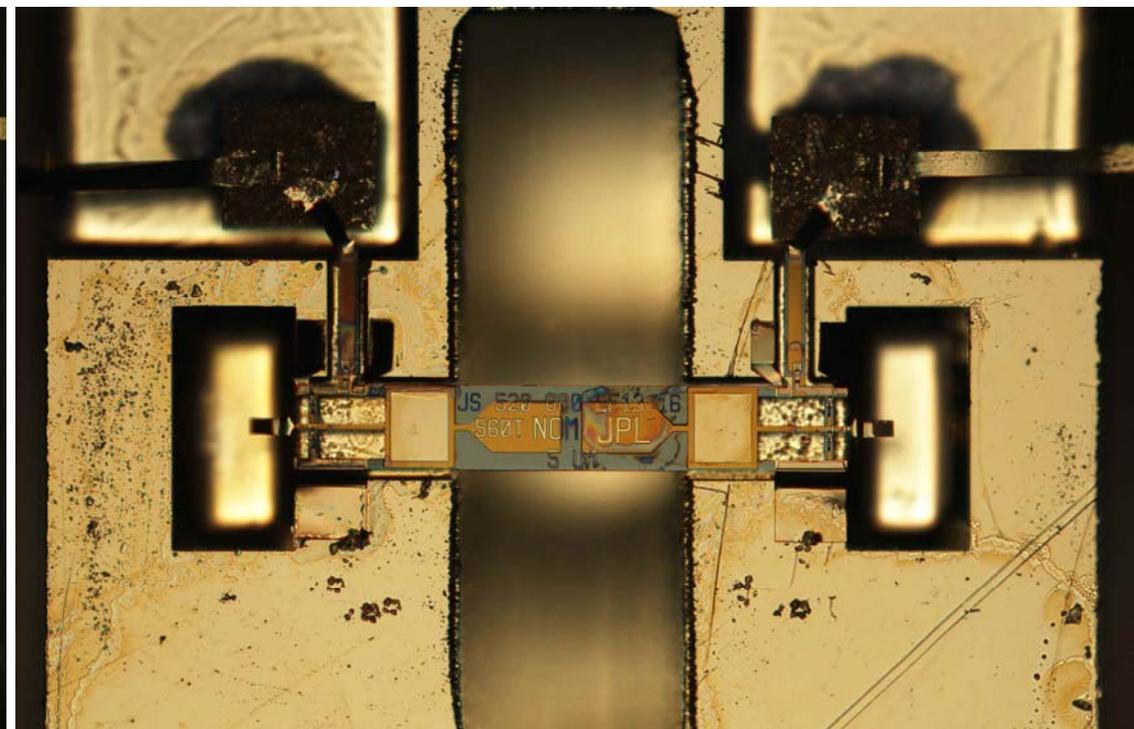
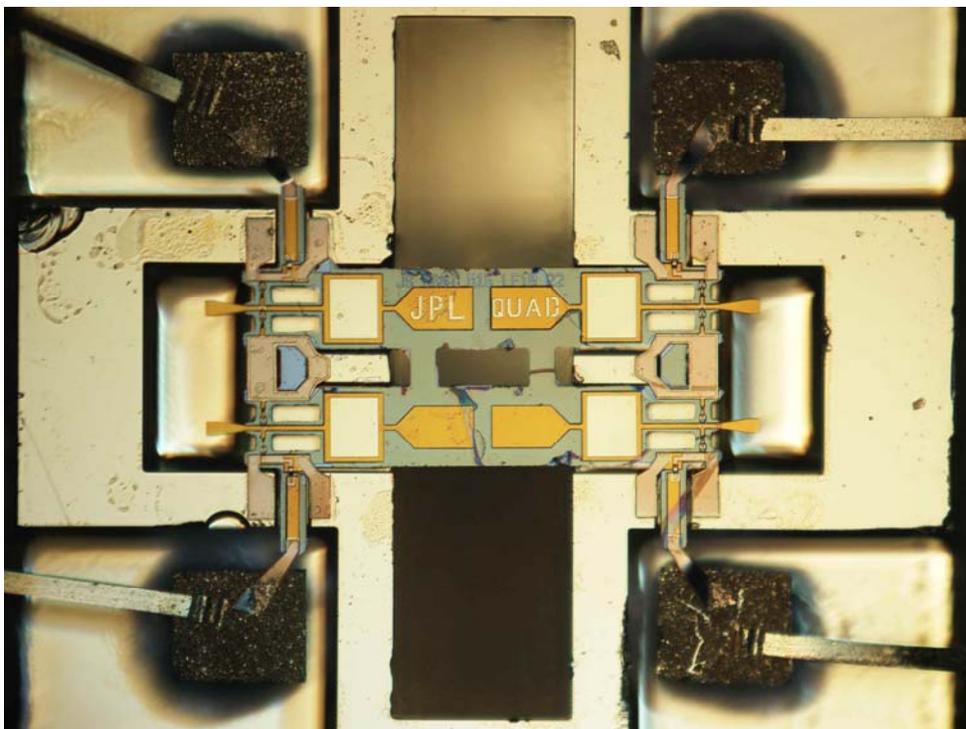
- Roughness from the DRIE process results in a roughness of 335nm—too high for these frequencies
- 2um of thermal oxide grown over wafer (1um into and 1um added to wafer)
- Oxide removed with wet etching
- Process smooth rough features since oxide will penetrate peaks more than valleys

# DRIE Components



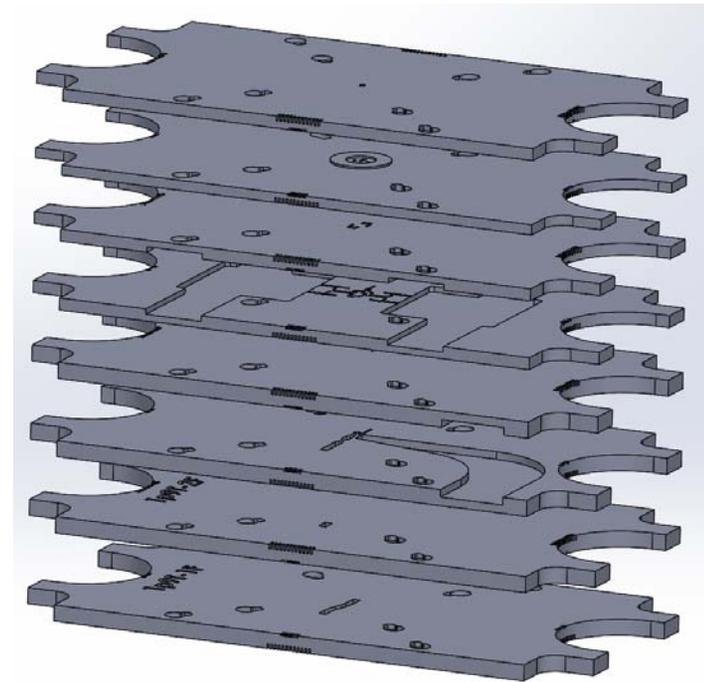
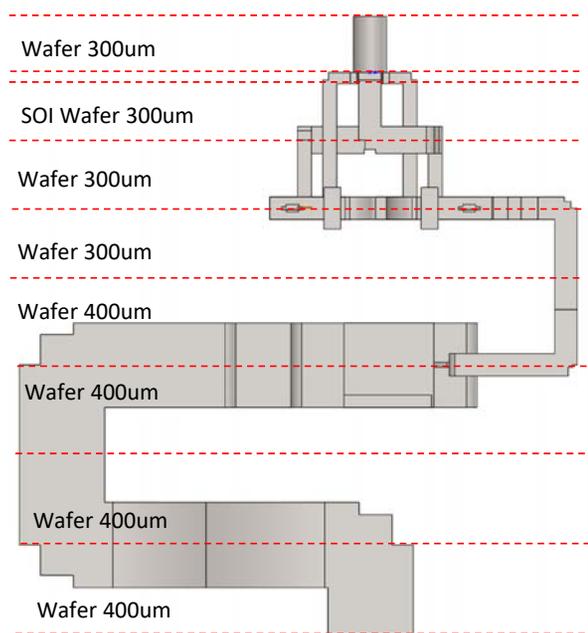
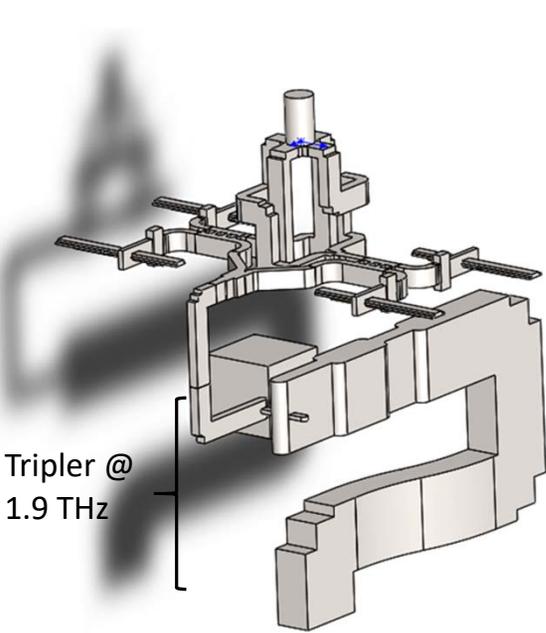
Different silicon micromachined layers before gold deposition.

# Integration of Active Devices

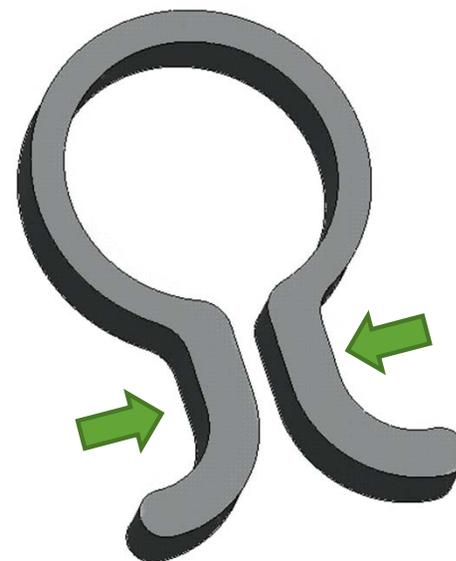
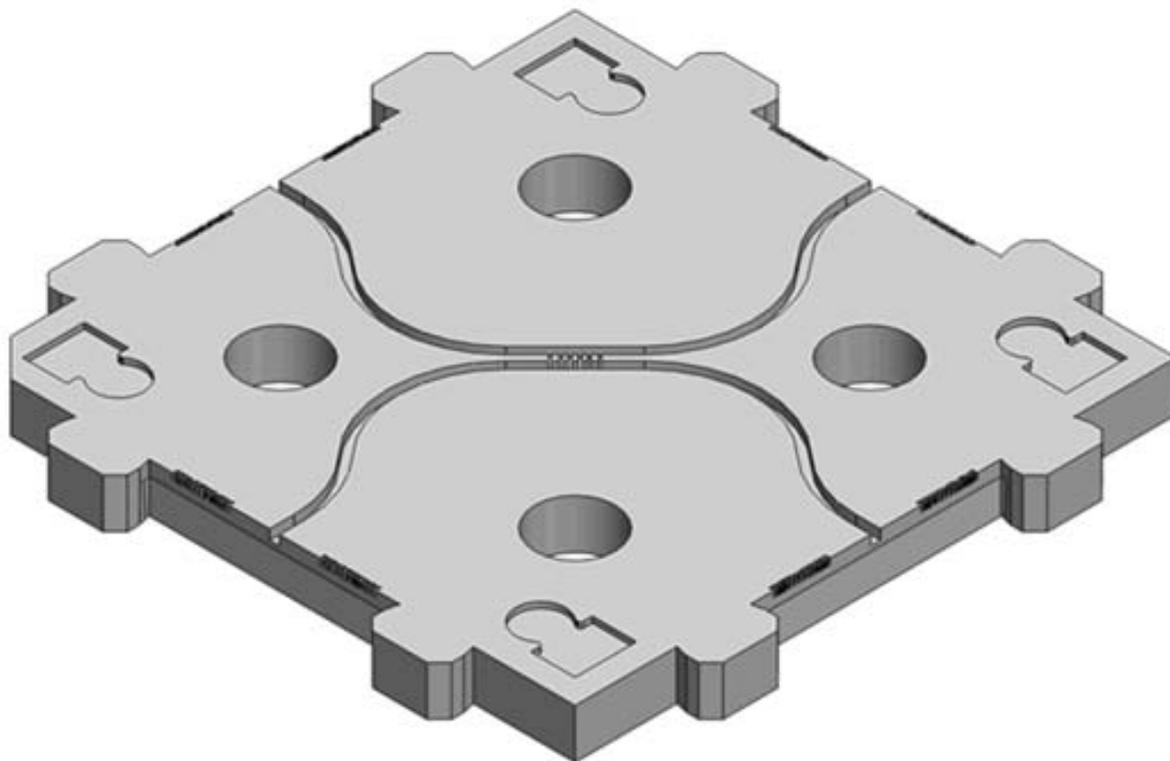


# Vertical Integration

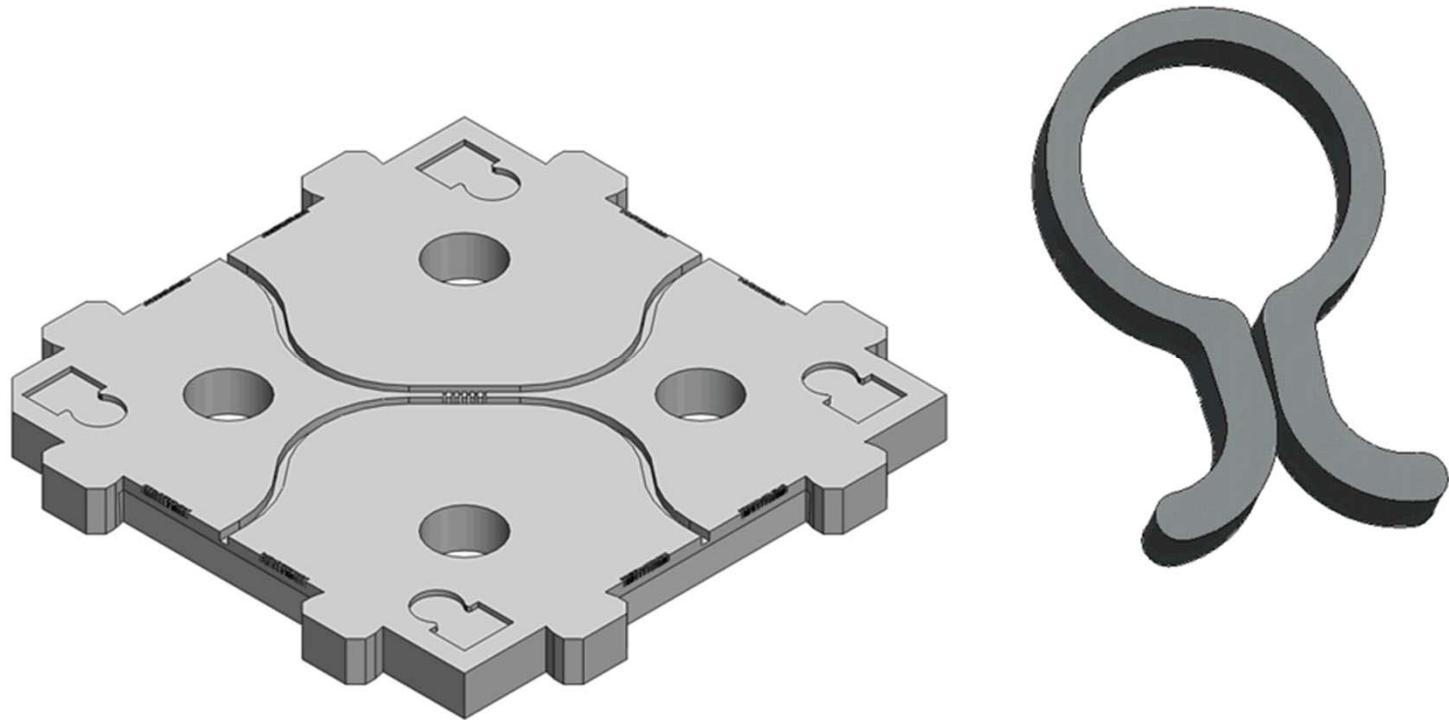
- Waveguide structures are fabricated on silicon wafers and coated with gold, stacked vertically



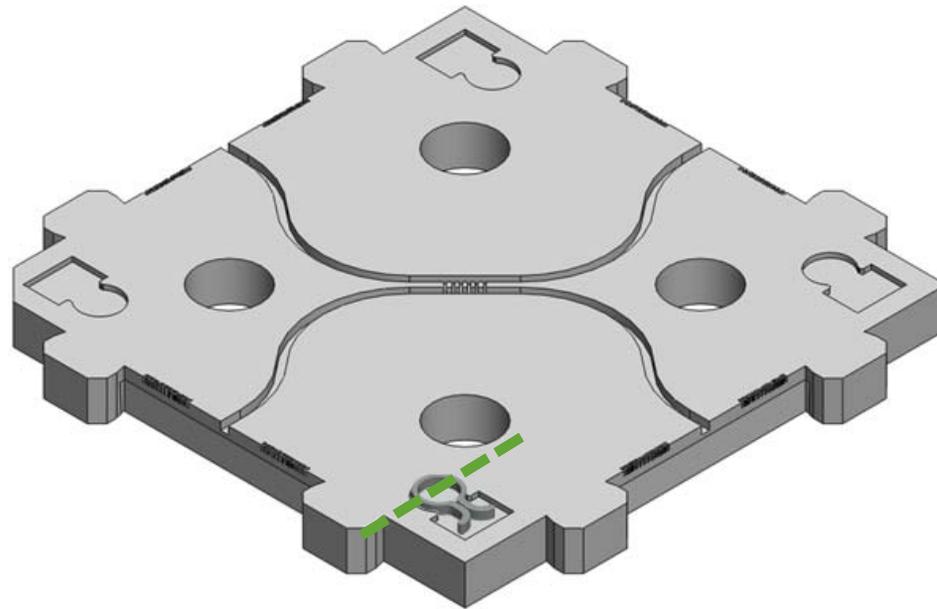
# Alignment of Silicon Wafers



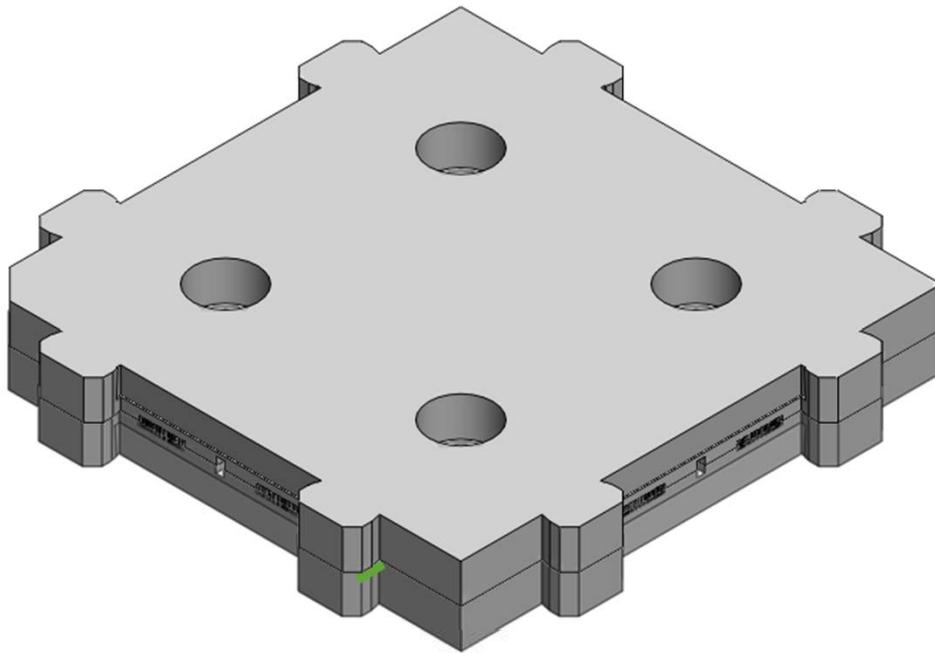
# Alignment of Silicon Wafers



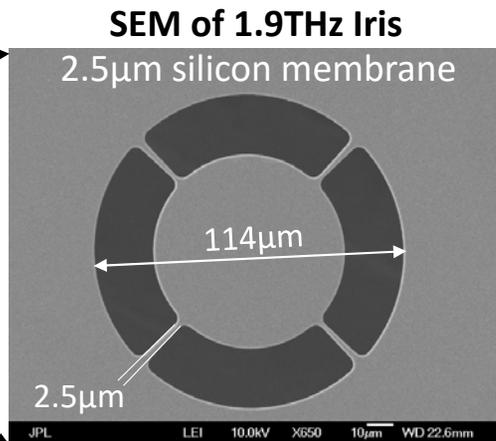
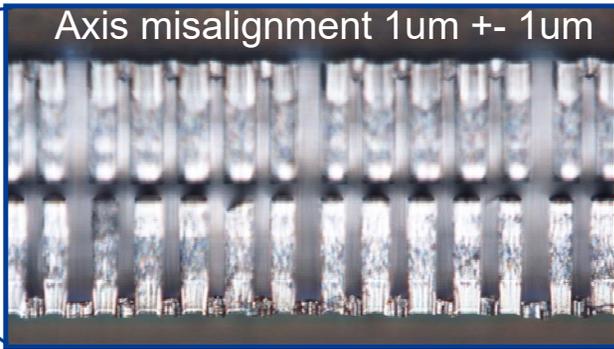
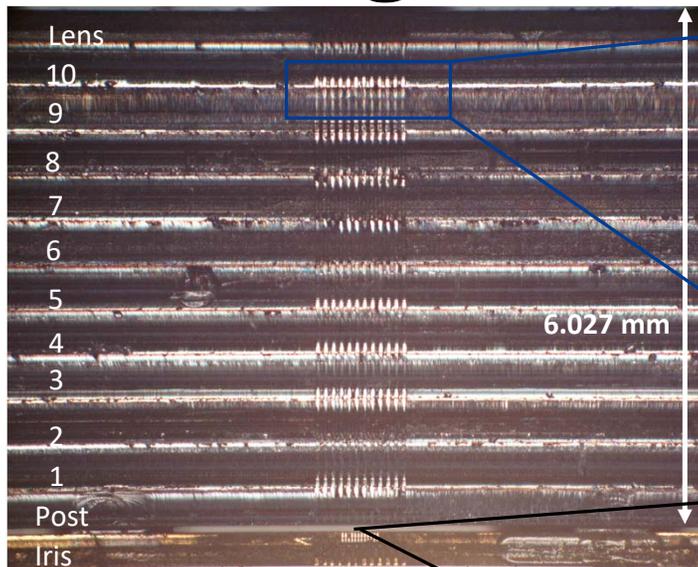
# Alignment of Silicon Wafers



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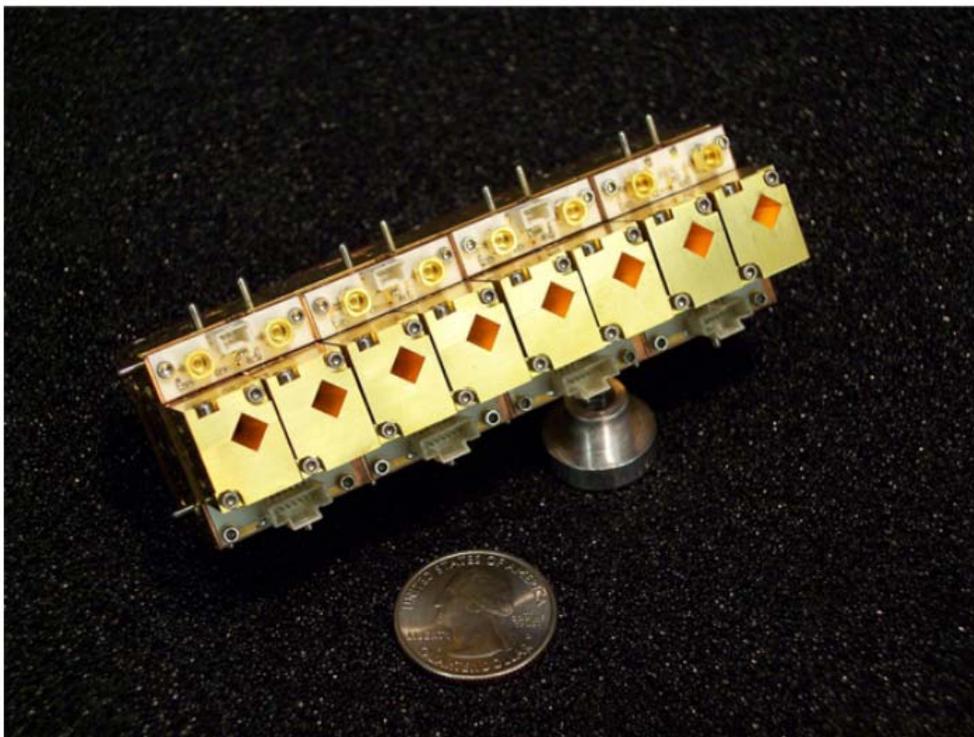


# Alignment of Silicon Wafers



**Alignment better than 1 $\mu\text{m}$ !**

# Integrated System



handgun,  
outside pocket of  
leather jacket



handgun,  
inside pocket of  
leather jacket



**8-Pixel Fully Functional 340 GHz Imaging Radar System.**



# Summary



- **Packaging is a challenge at millimeter-wavelengths**
- **It gets much harder at terahertz frequencies.**
- **Silicon micromachined waveguide based packaging seems to be a practical solution.**